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(54) Title: PROCESS FOR THE PREPARATION OF EPITAXIAL WAFERS FOR RESISTIVITY MEASUREMENTS

(57) Abstract

The present invention is directed to a process for evaluating a silicon wafer having a n–type or a p–type epitaxial layer on the surface thereof. In a first embodiment, an oxide layer is formed on the surface of a n–type epitaxial wafer by exposing the wafer to ultraviolet light while in the presence of oxygen. The wafer is then subjected to a capacitance–voltage measurement to evaluate the characteristics of the epitaxial layer. In a second embodiment, an oxide layer is dissolved from the surface of a p–type epitaxial wafer by passing a gaseous mixture comprising an inert carrier gas and hydrofluoric acid vapors over the surface of the wafer. The wafer is then subjected to a capacitance–voltage measurement to evaluate the characteristics of the epitaxial layer.